

ABSTRACT OF THE DISCLOSURE

5 A nonvolatile semiconductor memory device that can be
miniaturized is provided. A method of manufacturing the nonvolatile
semiconductor memory device includes the steps of: forming an interlayer
insulating film covering a stacked structure and a sidewall insulating film
and having a top surface approximately parallel to a main surface; forming a
resist pattern as a mask layer on the top surface of the interlayer insulating
film; forming a groove as an opening in the interlayer insulating film to be
positioned between the sidewall insulating films formed at the adjacent
10 stacked structures; and forming a source region extending along a plurality
of floating gate electrodes by implanting impurity ions from the groove to the
main surface.